

2010 年度業績 — 藤原 康文

学術論文・解説記事

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11. Y. Terai, T. Tsuji, K. Noda, and Y. Fujiwara, Photoluminescence properties of Er-doped β -FeSi₂ grown by ion beam synthesis methods, *Physica E*, 42, 2846–2848, 2010
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- Eu-doped ZnO films grown by sputtering-assisted metalorganic chemical vapor deposition, *Physica E*, 42, 2834–2836., 2010
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受賞

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2. 古川直樹, 学生優秀講演賞 (日本材料学会半導体エレクトロニクス部門委員会), 2010 年 5 月 17 日
3. 米田圭佑, 第 29 回応用物理学会講演奨励賞 (応用物理学会), 2011 年 3 月 24 日
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